Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM6K34TU

High Current Switching Applications
Power Management Switch Applications

• 4.5Vdrive

• Low on resistance: $:R_{on} = 77 \text{ m}\Omega \text{ (max) } (@V_{GS} = 4.5 \text{ V})$

 $:R_{on} = 50 \text{ m}\Omega \text{ (max) (@V_{GS} = 10 V)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit		
Drain-Source voltage		V_{DS}	30	V	
Gate-Source voltage		V _{GSS}	±20	V	
Drain current	DC	I _D	3	А	
	Pulse	I _{DP}	6		
Drain power dissipation		P _D (Note 1)	500	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	−55 ~ 150	°C	

Note:

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on FR4 board.

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ t}, \text{ Cu Pad: } 645 \text{ mm}^2)$

2.1±0.1 1.7±0.1 1.7±0.1 1.7±0.1 1.0±0.2 2.0±0.1 1.0±0.2 2.0±0.1 1.0±0.2 2.0±0.1 2.0±0.2 3.0±0.1 4.0±0.2 4.0±0.2 1.0

: Source

TOSHIBA 2-2T1D
Weight: 7.0 mg (typ.)

4

UF6

JEDEC

JEITA

Electrical Characteristics (Ta = 25°C)

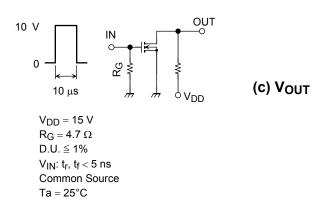
Character	ristics	Symbol	Test Condition		Min	Тур.	Max	Unit
Drain-Source breakdown voltage		V _{(BR)DSS}	$I_D = 10 \text{ mA}, V_{GS} = 0$		30	_	_	V
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_			
Drain cut-off current		I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0$		_	_	10	μΑ
Gate leakage current		I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$		_	_	±10	μΑ
Gate threshold voltage		V _{th}	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$		1.3	_	2.5	V
Forward transfer adm	ittance	Y _{fs}	V _{DS} = 10 V, I _D = 2 A	(Note2)	3.4	6.8	_	S
Drain-Source ON resistance		R _{DS} (ON)	$I_D = 2 A, V_{GS} = 4.5 V$	(Note2)	_	58	77	mΩ
			I _D = 2 A, V _{GS} = 10 V	(Note2)	_	38	50	
Input capacitance		C _{iss}			_	470		
Reverse transfer capacitance Output capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		_	60	_	pF
		Coss		_	80	_		
Total gate charge		Qg	V - 24 V I - 2 0 A		_	10	_	
Gate-source charge		Q _{gs}	V_{DS} = 24 V, I_{DS} = 3.0 A V_{GS} = 10 V		-	7.6	_	nC
Gate-drain charge		Q _{gd}			_	2.4	_	
Switching time	Turn-on time	t _{on}	$V_{DD} = 15 \text{ V}, I_D = 2 \text{ A},$		_	8.3	_	20
	Turn-off time	t _{off}	$V_{GS} = 0 \sim 10 \text{ V}, R_G = 4.7 \Omega$		_	22	_	ns
Drain-Source forward voltage		V _{DSF}	I _D = -3A, V _{GS} = 0V	(Note2)	_	-0.8	-1.2	V

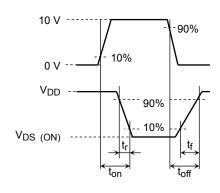
Note2: Pulse test

Switching Time Test Circuit

(a) Test Circuit

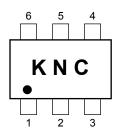
(b) V_{IN}

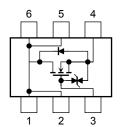




Marking

Equivalent Circuit (Top View)





Precaution

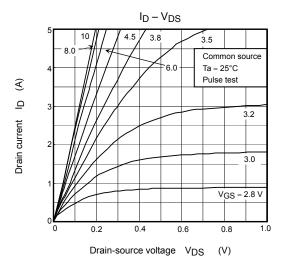
 V_{th} can be expressed as the voltage between gate and source when the low operating current value is I_D = 1 mA for this product. For normal switching operation, $V_{GS\ (on)}$ requires a higher voltage than V_{th} and $V_{GS\ (off)}$ requires a lower voltage than V_{th} .

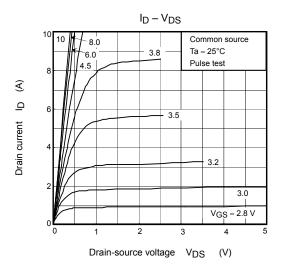
(The relationship can be established as follows: $V_{GS (off)} < V_{th} < V_{GS (on)}$.)

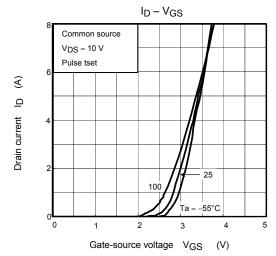
Take this into consideration when using the device.

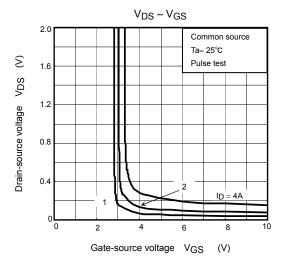
Handling Precaution

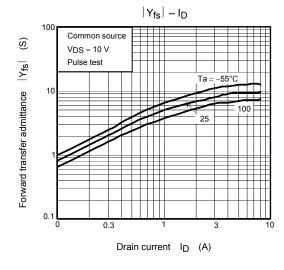
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

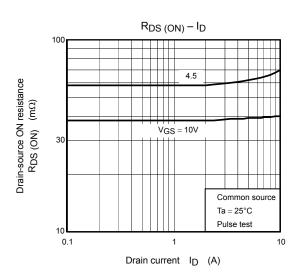


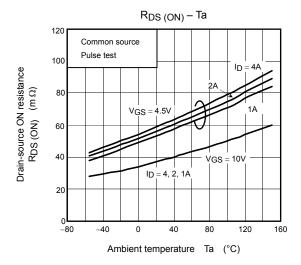


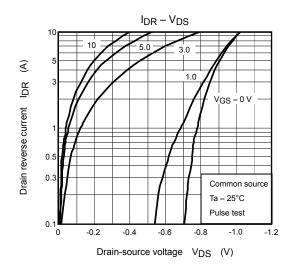


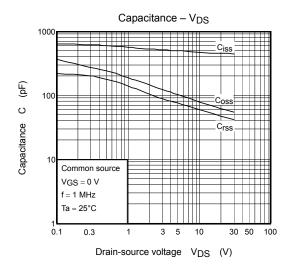


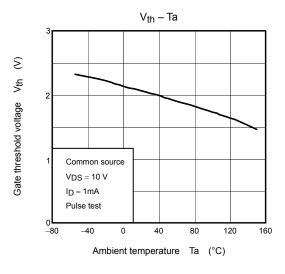


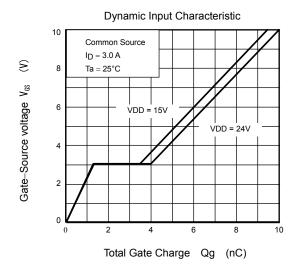


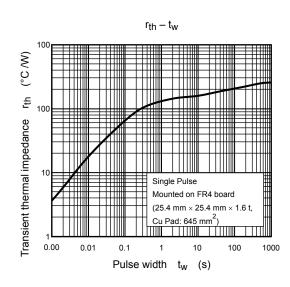












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20070701-EN GENERAL

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